MMST4401

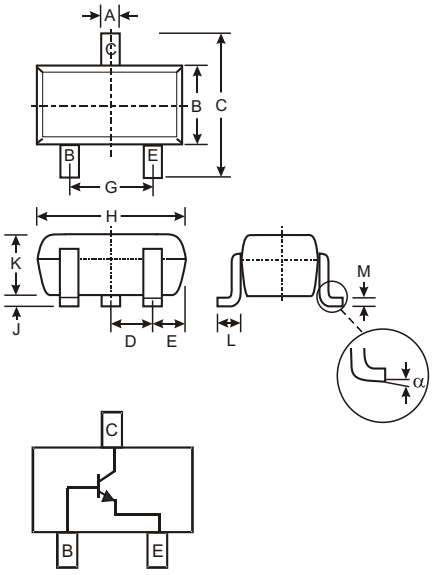
NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMST4403)
- Ultra-Small Surface Mount Package
- **Lead Free/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3 and 4)**

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking (See Page 2): K3X
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approximate)



SOT-323		
Dim	**Min**	**Max**
A	0.25	0.40
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
G	1.20	1.40
H	1.80	2.20
J	0.0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.18
	0	8
All Dimensions in mm		

Maximum Ratings @ T_A = 25 C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous (Note 1)	I_C	600	mA
Power Dissipation (Note 1)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	R_{JA}	625	C/W
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	C

Note:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
2. No purposefully added lead.
3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.products/lead_free/index.php.
4. Product manufactured with Date Code 0609 (week 9, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0609 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

Electrical Characteristics @ T_A = 25 C unless otherwise specified

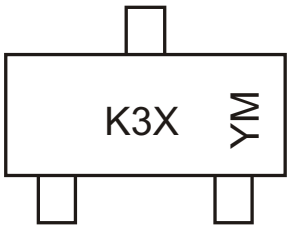
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60		V	I_C = 100 A, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40		V	I_C = 1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0		V	I_E = 100 A, I_C = 0
Collector Cutoff Current	I_{CEX}		100	nA	V_{CE} = 35V, $V_{EB(OFF)}$ = 0.4V
Base Cutoff Current	I_{BL}		100	nA	V_{CE} = 35V, $V_{EB(OFF)}$ = 0.4V
ON CHARACTERISTICS (Note 5)					
DC Current Gain	h_{FE}	20 40 80 100 40	300		I_C = 100µA, V_{CE} = 1.0V I_C = 1.0mA, V_{CE} = 1.0V I_C = 10mA, V_{CE} = 1.0V I_C = 150mA, V_{CE} = 1.0V I_C = 500mA, V_{CE} = 2.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$		0.40 0.75	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.75	0.95 1.2	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{cb}		6.5	pF	V_{CB} = 5.0V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{eb}		30	pF	V_{EB} = 0.5V, f = 1.0MHz, I_C = 0
Input Impedance	h_{ie}	1.0	15	k	V_{CE} = 10V, I_C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h_{re}	0.1	8.0	x 10^{-4}	
Small Signal Current Gain	h_{fe}	40	500		
Output Admittance	h_{oe}	1.0	30	S	
Current Gain-Bandwidth Product	f_T	250		MHz	V_{CE} = 10V, I_C = 20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d		15	ns	V_{CC} = 30V, I_C = 150mA, $V_{BE(off)}$ = 2.0V, I_{B1} = 15mA
Rise Time	t_r		20	ns	
Storage Time	t_s		225	ns	V_{CC} = 30V, I_C = 150mA, I_{B1} = I_{B2} = 15mA
Fall Time	t_f		30	ns	

Ordering Information (Note 4 & 6)

Device	Packaging	Shipping
MMST4401-7-F	SOT-323	3000/Tape & Reel

Notes:
4. Product manufactured with Date Code 0609 (week 9, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0609 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.
5. Short duration test pulse used to minimize self-heating effect.
6. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf

Marking Information



K3X = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

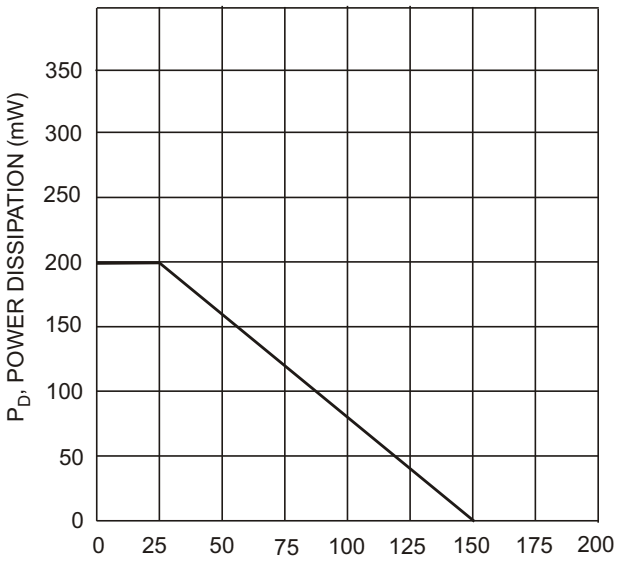


Fig. 1, Max Power Dissipation vs Ambient Temperature

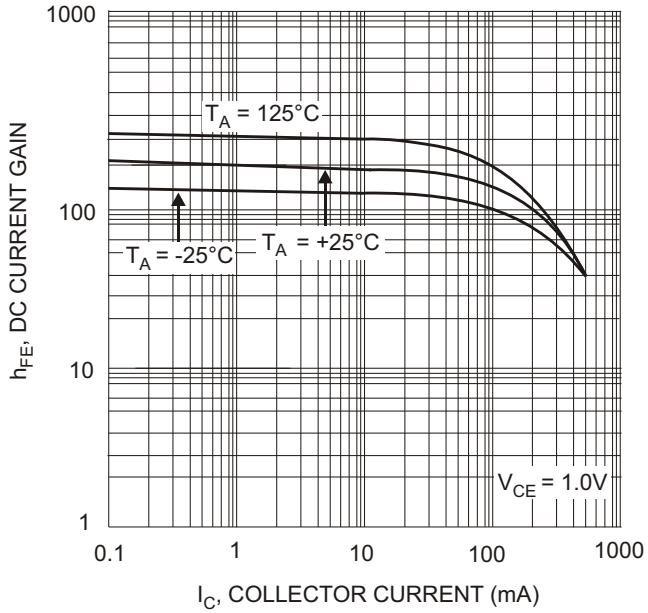


Fig. 2 Typical DC Current Gain vs Collector Current

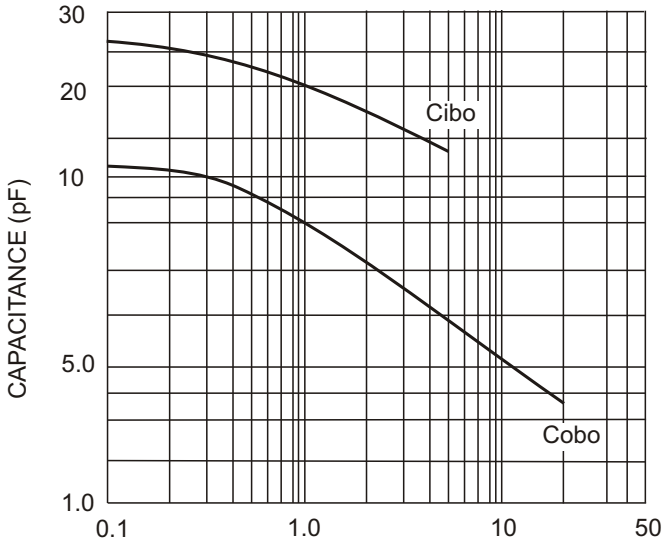


Fig. 3 Typical Capacitance

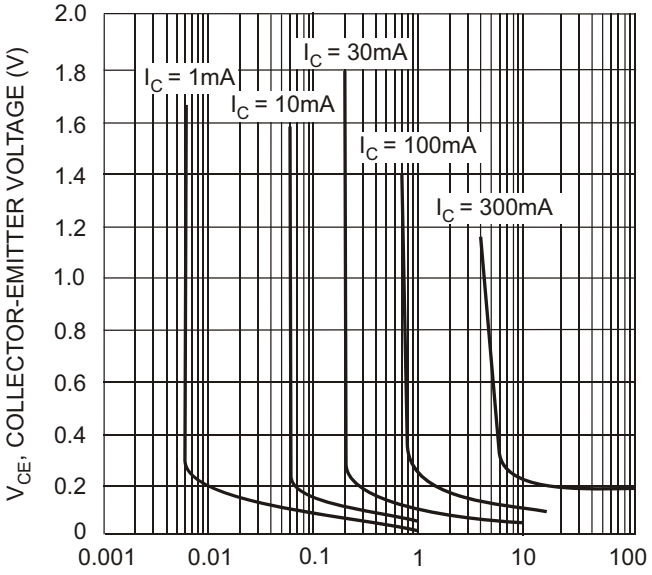


Fig. 4 Typical Collector Saturation Region

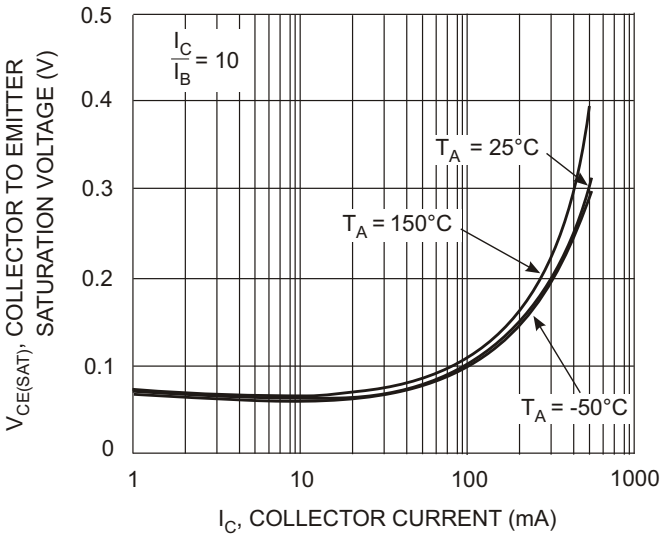


Fig. 5 Collector Emitter Saturation Voltage vs. Collector Current

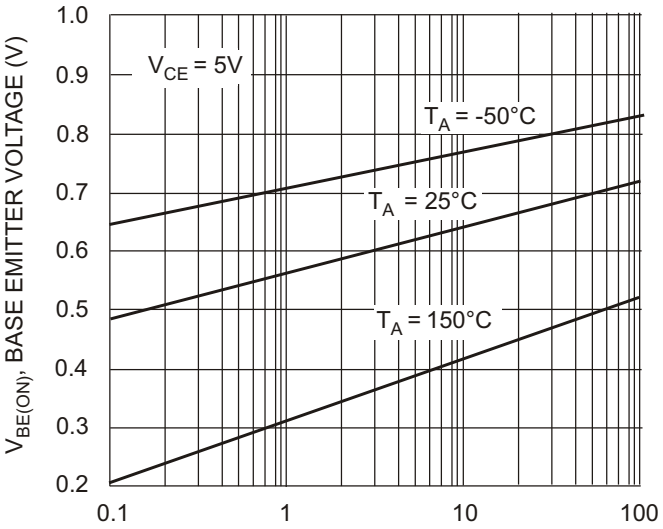


Fig. 6 Base Emitter Voltage vs. Collector Current

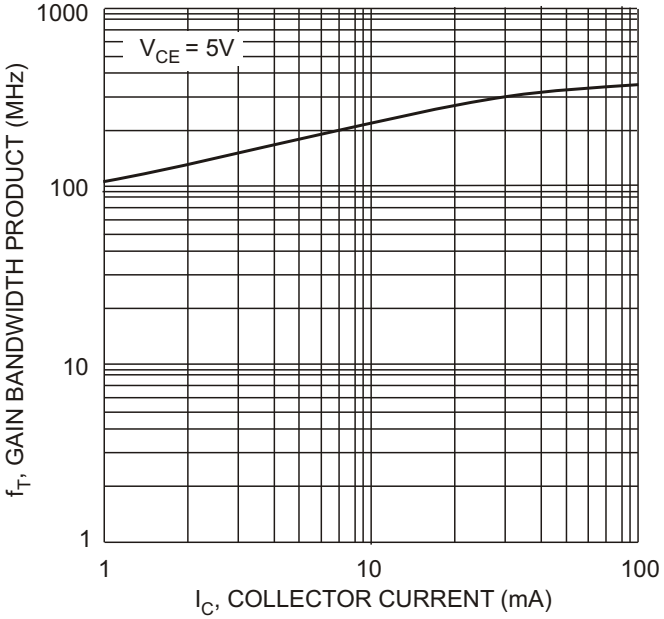


Fig. 7 Gain Bandwidth Product vs. Collector Current